

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|------|------------------------------|--|----------------------|
| 1 | BRS | L1 | 1 | hocheng near hong.in. | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/0 1 14:27 |
| 2 | BRS | L2 | 0 | huang near yun- liang.in. | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/0 1 14:28 |
| 3 | BRS | L3 | 2004 | 438/692.ccls. | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/0 1 14:29 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|------|--|--|------------------|
| 4 | BRS | L4 | 271 | 3 and (endpoint or end-point) | US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/01 14:30 |
| 5 | BRS | L6 | 0 | 3 and (endpoint or end-point) near5 (cmp) near15 (slope) | US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/01 14:33 |
| 6 | BRS | L5 | 129 | 3 and (endpoint or end-point) near5 cmp | US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/01 14:31 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|------|--|--|------------------|
| 7 | BRS | L7 | 3 | 3 and (endpoint or end-point) near5 (cmp) near15 (temp) | US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/01 14:34 |
| 8 | BRS | L8 | 3 | 3 and (endpoint or end-point) near5 (cmp) near15 (temperature) | US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/01 14:35 |
| 9 | BRS | L9 | 0 | 3 and (slope) near5 (cmp) near15 (temperature) | US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/01 14:35 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|---|--|----------------------|
| 10 | BRS | L10 | 0 | (slope) near5 (cmp) near15 (temperature) | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/0 1 14:35 |
| 11 | BRS | L11 | 0 | (slope) near25 (cmp) near15 (temperature) | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/0 1 14:35 |
| 12 | BRS | L12 | 18 | (endpoint or end- point) near5 (cmp) near15 (temperature) | US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB | 2004/12/0 1 14:35 |

| | U | 1 | Document ID | Title | Current OR |
|----|---|---|-------------------------|---|------------|
| 1 | | | US 20040080757 A1 | Integrated surface metrology | 356/601 |
| 2 | | | US 20030077995 A1 | Chemical mechanical polishing slurry | 451/528 |
| 3 | | | US 20030045100 A1 | In-situ method and apparatus for end point detection in chemical mechanical polishing | 438/689 |
| 4 | | | US 20020173252 A1 | Chemical mechanical polishing | 451/259 |
| 5 | | | US 20020023338 A1 | Method for making a magnetoresistive sensor | 29/603.15 |
| 6 | | | US 20020022372 A1 | Method for reducing micro-particle adsorption effects | 438/692 |
| 7 | | | US 6798529 B2 | In-situ method and apparatus for end point detection in chemical mechanical polishing | 356/630 |
| 8 | | | US 6690473 B1 | Integrated surface metrology | 356/601 |
| 9 | | | US 6676492 B2 | Chemical mechanical polishing | 451/65 |
| 10 | | | US 6517413 B1 | Method for a copper CMP endpoint detection system | 451/6 |
| 11 | | | US 6503124 B1 | Method for endpoint detection for copper CMP | 451/6 |

| | U | 1 | Document ID | Title | Current OR |
|----|---|---|------------------|--|------------|
| 12 | | | US 6479387 B2 | Method for reducing micro-particle adsorption effects | 438/692 |
| 13 | | | US 6458017 B1 | Planarizing method | 451/28 |
| 14 | | | US 6179691 B1 | Method for endpoint detection for copper CMP | 451/41 |
| 15 | | | US 5647952 A | Chemical/mechanical polish (CMP) endpoint method | 438/8 |
| 16 | | | US 5597442 A | Chemical/mechanical planarization (CMP) endpoint method using measurement of polishing pad temperature | 438/8 |
| 17 | | | US 5196353 A | Method for controlling a semiconductor (CMP) process by measuring a surface temperature and developing a thermal image of the wafer | 438/5 |

| | U | 1 | Document ID | Title | Current OR |
|----|---|---|-------------|---|------------|
| 18 | | | TW 299462 A | Polishing endpoint detection method for CMP - using IR temperature detection device to detect change of temperature at endpoint when removing one material and exposing second material | |